

# Hex 3-State Noninverting Buffer with Common Enables

**High-Performance Silicon-Gate CMOS** 

# MC74HC365A, MC74HCT365A

The MC74HC365A/MC74HCT365A is identical in pinout to the LS365. The MC74HC365A inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. The MC74HCT365A inputs are compatible with LSTTL outputs.

This device is a high-speed hex buffer with 3-state outputs and two common active-low Output Enables. When either of the enables is high, the buffer outputs are placed into high-impedance states. The HC365A, HCT365A has noninverting outputs.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V (HC), 4.5 to 5.5 V (HCT)
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 90 FETs or 22.5 Equivalent Gates
- –Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

1



SOIC-16 D SUFFIX CASE 751B

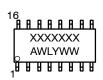


TSSOP-16 DT SUFFIX CASE 948F



QFN16 MN SUFFIX CASE 485AW

#### MARKING DIAGRAMS







A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 8 of this data sheet.

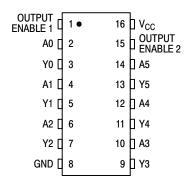


Figure 1. Pin Assignment

### **FUNCTION TABLE**

	Inputs				
Enable 1	Enable Enable 1 2		Y		
L	L	L	L		
L	L	Н	Н		
Н	Х	X	Z		
Х	Н	Х	Z		

X = don't care

Z = high impedance

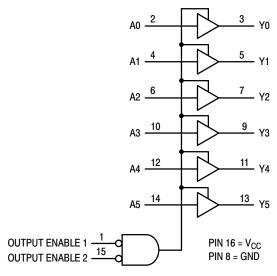


Figure 2. Logic Diagram

#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +6.5	V	
V <sub>IN</sub>	DC Input Voltage		-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IN</sub>	DC Input Current, per Pin		±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins		±50	mA
I <sub>IK</sub>	Input Clamp Current (V <sub>IN</sub> < 0 or V <sub>IN</sub> > V <sub>CC</sub> )		±20	mA
lok	Output Clamp Current (V <sub>OUT</sub> < 0 or V <sub>OUT</sub> > V <sub>CC</sub> )		±20	mA
T <sub>STG</sub>	Storage Temperature		−65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		±150	°C
θЈА	Thermal Resistance (Note 1)	SOIC-16 QFN16 TSSOP-16	126 118 159	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 25°C	SOIC-16 QFN16 TSSOP-16	995 1062 787	mW
MSL	Moisture Sensitivity		Level 1	_
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V <sub>ESD</sub>	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
MC74HC				
V <sub>CC</sub>	DC Supply Voltage	2.0	6.0	V
V <sub>IN,</sub> V <sub>OUT</sub>	DC Input, Output Voltage (Note 3)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free-Air Temperature	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $V_{CC} = 2.0 \text{ V} \\ V_{CC} = 3.0 \text{ V} \\ V_{CC} = 4.5 \text{ V} \\ V_{CC} = 6.0 \text{ V}$	0 0 0 0	1000 600 500 400	ns
MC74HCT				
V <sub>CC</sub>	DC Supply Voltage	4.5	5.5	V
V <sub>IN,</sub> V <sub>OUT</sub>	DC Input, Output Voltage (Note 3)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free-Air Temperature	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

## DC ELECTRICAL CHARACTERISTICS (MC74HC365A)

				Guaranteed Limit				
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	–55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit	
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V	
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V	
		$ \begin{aligned} V_{in} &= V_{IH} & \begin{vmatrix} I_{out} \\ I_{out} \end{vmatrix} \leq 3.6 \text{ mA} \\ \begin{vmatrix} I_{out} \\ I_{out} \end{vmatrix} \leq 6.0 \text{ mA} \\ \begin{vmatrix} I_{out} \\ 1 \end{vmatrix} \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V	
		$ \begin{aligned} V_{in} &= V_{IL} & \begin{vmatrix} I_{out} \\ I_{out} \end{vmatrix} \leq 3.6 \text{ mA} \\ \begin{vmatrix} I_{out} \\ I_{out} \end{vmatrix} \leq 6.0 \text{ mA} \\ \begin{vmatrix} I_{out} \\ 0 \end{bmatrix} \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40		
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ	
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	±0.5	±5.0	±10	μΑ	
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (MC74HC365A)

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub> V	–55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 4)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>			220 110 44 37	275 140 55 47	330 170 66 56	ns
t <sub>PZL</sub> , t <sub>PZH</sub>			220 110 44 37	275 140 55 47	330 170 66 56	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	60	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. \*Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ .

## DC ELECTRICAL CHARACTERISTICS (MC74HCT365A)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	–55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\  I_{out}  &\leq 20  \mu\text{A} \end{aligned}$	4.5 to 5.5	2.0	2.0	2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 to 5.5	0.8	0.8	0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	4.5	4.4	4.4	4.4	V
		$V_{in} = V_{IH}  I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5	0.1	0.1	0.1	٧
		$V_{in} = V_{IL}  I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	4.5	±0.1	±1.0	±1.0	μА
I <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	4.5	±0.5	±5.0	±10	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	4.5	4	40	160	μΑ

	Additional Quiescent Supply	V <sub>in</sub> = 2.4 V, Any One Input		≥-55°C	25 to 125°C	
$\Delta I_{CC}$	Current	$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0 \mu A$	5.5	2.9	2.4	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

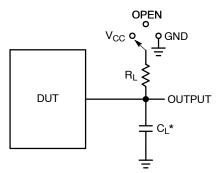
### AC ELECTRICAL CHARACTERISTICS (MC74HCT365A)

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub> V	–55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 3 and 4)	4.5	24	30	36	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>			44	55	66	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	· (F: 0 1.4)		44	55	66	ns
t <sub>TLH</sub> , t <sub>THL</sub>			12	15	18	ns
C <sub>in</sub>	C <sub>in</sub> Maximum Input Capacitance		10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

		Typical	@ 25°C, V <sub>C</sub>	<sub>C</sub> = 5.0 V		Ī
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	60			pF	

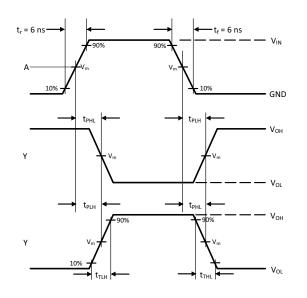
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. \*Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \, V_{CC}^2 f + I_{CC} \, V_{CC}$ .

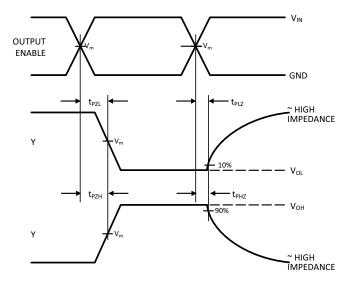
## **SWITCHING WAVEFORMS**



Test	Switch Position	C <sub>L</sub>	R <sub>L</sub>
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	50 pF	1 kΩ
t <sub>PLZ</sub> / t <sub>PZL</sub>	V <sub>CC</sub>		
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND		

Figure 3. Test Circuit





Device	$V_{IN}, V$	V <sub>m</sub> , V
MC74HC365A	V <sub>CC</sub>	50% x V <sub>CC</sub>
MC74HCT365A	3 V	1.3 V

Figure 4. Switching Waveforms

 $<sup>^{\</sup>star}C_{L}$  Includes probe and jig capacitance

## **TEST CIRCUITS**

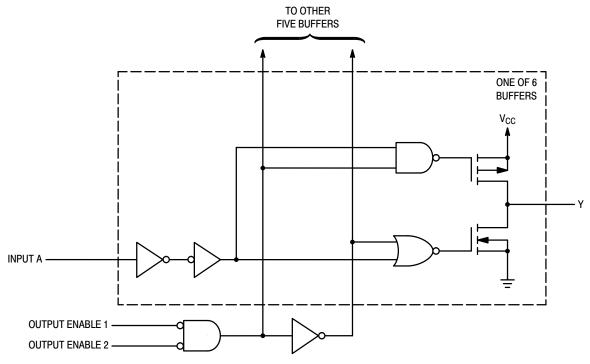


Figure 5. Logic Detail

## **ORDERING INFORMATION**

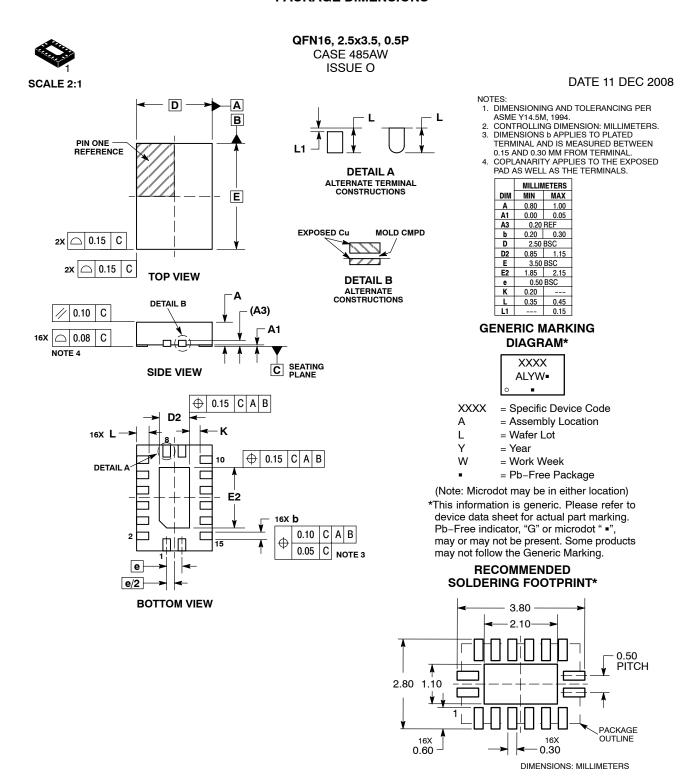
Device	Marking	Package	Shipping <sup>†</sup>
MC74HC365ADR2G	HC365AG	SOIC-16	2500 / Tape & Reel
MC74HC365ADTR2G	HC 365A	TSSOP-16	2500 / Tape & Reel
MC74HC365ADTR2G-Q*	HC 365A	TSSOP-16	2500 / Tape & Reel
MC74HCT365ADR2G	HCT365AG	SOIC-16	2500 / Tape & Reel
MC74HCT365ADTR2G	HCT 365A	TSSOP-16	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.

\*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### PACKAGE DIMENSIONS



\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



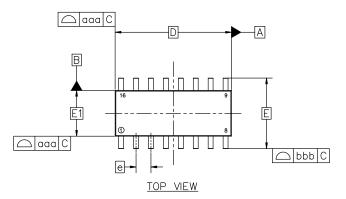


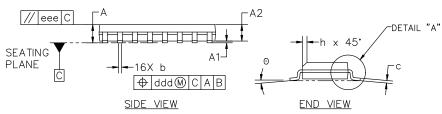
### SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

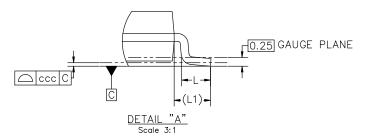
#### **DATE 29 MAY 2024**

#### NOTES:

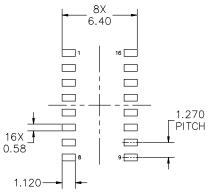
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS					
DIM	MIN NOM MAX				
Α	1.35	1.55	1.75		
A1	0.00	0.05	0.10		
A2	1.35	1.50	1.65		
b	0.35	0.42	0.49		
С	0.19	0.22	0.25		
D		9.90 BSC			
E	6.00 BSC				
E1	3.90 BSC				
е	1.27 BSC				
h	0.25 0.50				
L	0.40	0.83	1.25		
L1	1.05 REF				
Θ	0 7.				
TOLERANCE OF FORM AND POSITION					
aaa	0.10				
bbb	0.20				
ccc	0.10				
ddd	0.25				
eee	0.10				



### RECOMMENDED MOUNTING FOOTPRINT

\*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

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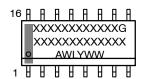
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### SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

**DATE 29 MAY 2024** 

# GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

077/15/		077/15.0		077/15.0		T/15 4	
STYLE 1: PIN 1.	COLLECTOR	STYLE 2:	CATHODE	STYLE 3: PIN 1.		TYLE 4: PIN 1.	COLLECTOR DVF #1
PIN 1. 2.		PIN 1. 2.		PIN 1. 2.	COLLECTOR, DYE #1 BASE, #1	PIN 1. 2.	
2. 3.	EMITTER	2. 3.	NO CONNECTION	2. 3.		2. 3.	
3. 4.	NO CONNECTION	3. 4.		3. 4.		3. 4.	
	EMITTER	4. 5.					
5.	BASE	5. 6.	NO CONNECTION	5.	,	5.	
6. 7.		o. 7.		6.	EMITTER, #2	6.	
7. 8.		7. 8.	CATHODE	7. 8.			COLLECTOR, #4 COLLECTOR, #4
8. 9.		8. 9.			COLLECTOR, #2		BASE, #4
9. 10.			ANODE		BASE. #3		EMITTER, #4
	NO CONNECTION						
	EMITTER	11.	CATHODE		EMITTER, #3 COLLECTOR, #3		BASE, #3
							EMITTER, #3
	BASE		CATHODE		COLLECTOR, #4		BASE, #2
	COLLECTOR	14.			BASE, #4		EMITTER, #2
15.			ANODE		EMITTER, #4		BASE, #1
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	,	PIN 1.		PIN 1.			
PIN 1. 2.	DRAIN, #1	PIN 1. 2.	CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3.	DRAIN, #1 DRAIN, #2	PIN 1. 2. 3.	CATHODE CATHODE	PIN 1. 2. 3.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4.	DRAIN, #1 DRAIN, #2 DRAIN, #2	PIN 1. 2. 3. 4.	CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	PIN 1. 2. 3. 4. 5. 6.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4	PIN 1. 2. 3. 4. 5. 6.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 GATE, #4 SOURCE, #4 SOURCE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GOMMON DRAIN (OUTPUT) GATE N-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 GATE, #1	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		

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2X L/2

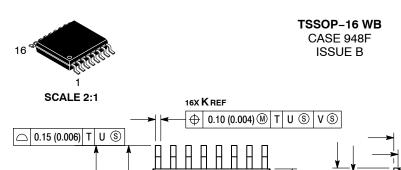
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☐ 0.15 (0.006)

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**DATE 19 OCT 2006** 

#### NOTES

Κ

SECTION N-N

0.25 (0.010)

J1

В

-U-

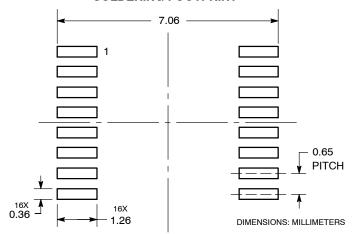
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABILE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	00	00	00	00

# **DETAIL E** -W-☐ 0.10 (0.004) **DETAIL E** SEATING PLANE D

#### **RECOMMENDED** SOLDERING FOOTPRINT\*

-V-



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **GENERIC** MARKING DIAGRAM\*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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